

# Andrew I Yakimov

## List of Publications by Year in descending order

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158  
papers

1,934  
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304368

22  
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329751

37  
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159  
all docs

159  
docs citations

159  
times ranked

996  
citing authors

#	ARTICLE	IF	CITATIONS
1	Normal-incidence infrared photoconductivity in Si p-i-n diode with embedded Ge self-assembled quantum dots. Applied Physics Letters, 1999, 75, 1413-1415.	1.5	108
2	Silicon-germanium nanostructures with quantum dots: Formation mechanisms and electrical properties. Semiconductors, 2000, 34, 1229-1247.	0.2	104
3	Interlevel Ge/Si quantum dot infrared photodetector. Journal of Applied Physics, 2001, 89, 5676-5681.	1.1	91
4	Molecular beam epitaxy of silicon-germanium nanostructures. Thin Solid Films, 2000, 367, 75-84.	0.8	80
5	Electronic states in Ge-Si quantum dots with type-II band alignment initiated by space-charge spectroscopy. Physical Review B, 2006, 73, .	1.1	65
6	Electronic structure of Ge/Si quantum dots. Nanotechnology, 2002, 13, 75-80.	1.3	62
7	Long-range Coulomb interaction in arrays of self-assembled quantum dots. Physical Review B, 2000, 61, 10868-10876.	1.1	60
8	Interband absorption in charged Ge/Si type-II quantum dots. Physical Review B, 2001, 63, .	1.1	51
9	Conductance oscillations in Ge/Si heterostructures containing quantum dots. Journal of Physics Condensed Matter, 1994, 6, 2573-2582.	0.7	42
10	In situ RHEED control of self-organized Ge quantum dots. Thin Solid Films, 2000, 380, 158-163.	0.8	41
11	Hopping conduction and field effect in Si modulation-doped structures with embedded Ge quantum dots. Physical Review B, 1999, 59, 12598-12603.	1.1	39
12	“Coulomb staircase” in a Si/Ge structure. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1992, 65, 701-705.	0.6	34
13	Formation of zero-dimensional hole states in Ge/Si heterostructures probed with capacitance spectroscopy. Thin Solid Films, 1998, 336, 332-335.	0.8	34
14	Stark effect in type-II Ge/Si quantum dots. Physical Review B, 2003, 67, .	1.1	34
15	Excitons in charged Ge/Si type-II quantum dots. Semiconductor Science and Technology, 2000, 15, 1125-1130.	1.0	31
16	Photovoltaic Ge/SiGe quantum dot mid-infrared photodetector enhanced by surface plasmons. Optics Express, 2017, 25, 25602.	1.7	30
17	Ge/Si photodiodes with embedded arrays of Ge quantum dots for the near infrared (1.3–1.5 $\mu\text{m}$ ) region. Semiconductors, 2003, 37, 1345-1349.	0.2	29
18	Phononless hopping conduction in two-dimensional layers of quantum dots. JETP Letters, 2003, 77, 376-380.	0.4	26

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19	Effect of the growth rate on the morphology and structural properties of hut-shaped Ge islands in Si(001). <i>Nanotechnology</i> , 2006, 17, 4743-4747.	1.3	26
20	Magnetic correlations on the insulating side of the metal-insulator transition in amorphous Si <sub>1-x</sub> Mnx. <i>Physical Review B</i> , 1995, 51, 16549-16552.	1.1	24
21	Effect of pulsed laser action on hole-energy spectrum of Ge <sup>+</sup> Si self-assembled quantum dots. <i>Physical Review B</i> , 2005, 72, .	1.1	22
22	Calculating the energy spectrum and electronic structure of two holes in a pair of strained Ge/Si coupled quantum dots. <i>Physical Review B</i> , 2010, 81, .	1.1	22
23	Germanium Self-Assembled Quantum Dots in Silicon for Nano- and Optoelectronics. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2006, 1, 119-175.	0.1	22
24	Raman scattering of Ge dot superlattices. <i>European Physical Journal B</i> , 2000, 16, 355-359.	0.6	21
25	Depolarization shift of the in-plane polarized interlevel resonance in a dense array of quantum dots. <i>Physical Review B</i> , 2000, 62, 9939-9942.	1.1	21
26	Type-II Ge/Si quantum dots. <i>Semiconductors</i> , 2001, 35, 1095-1105.	0.2	21
27	Spatial separation of electrons in Ge/Si(001) heterostructures with quantum dots. <i>JETP Letters</i> , 2001, 73, 529-531.	0.4	20
28	Influence of delta-doping on the performance of Ge/Si quantum-dot mid-infrared photodetectors. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	20
29	Photoconductive gain and quantum efficiency of remotely doped Ge/Si quantum dot photodetectors. <i>Materials Research Express</i> , 2016, 3, 105032.	0.8	20
30	Plasmon polariton enhanced mid-infrared photodetectors based on Ge quantum dots in Si. <i>Journal of Applied Physics</i> , 2017, 122, .	1.1	20
31	Low-dimensional hopping conduction in porous amorphous silicon. <i>Physica B: Condensed Matter</i> , 1995, 205, 298-304.	1.3	19
32	Surface plasmon dispersion in a mid-infrared Ge/Si quantum dot photodetector coupled with a perforated gold metasurface. <i>Applied Physics Letters</i> , 2018, 112, 171107.	1.5	18
33	Hole states in Ge <sup>+</sup> Si quantum-dot molecules produced by strain-driven self-assembly. <i>Journal of Applied Physics</i> , 2007, 102, 093714.	1.1	17
34	Enhanced oscillator strength of interband transitions in coupled Ge <sup>+</sup> Si quantum dots. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	16
35	Effect of overgrowth temperature on the mid-infrared response of Ge/Si(001) quantum dots. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	16
36	Electronic states in vertically ordered Ge/Si quantum dots detected by photocurrent spectroscopy. <i>Physical Review B</i> , 2014, 90, .	1.1	16

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37	Evidence for a negative interband photoconductivity in arrays of Ge/Si type-II quantum dots. <i>Physical Review B</i> , 2000, 62, R16283-R16286.	1.1	15
38	Evidence for two-dimensional correlated hopping in arrays of Ge/Si quantum dots. <i>Physical Review B</i> , 2003, 68, .	1.1	15
39	Bonding-antibonding ground-state transition in coupled Ge/Si quantum dots. <i>Semiconductor Science and Technology</i> , 2009, 24, 095002.	1.0	15
40	Broadband Ge/SiGe quantum dot photodetector on pseudosubstrate. <i>Nanoscale Research Letters</i> , 2013, 8, 217.	3.1	15
41	Phonon bottleneck in <i>p</i> -type Ge/Si quantum dots. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	15
42	Localization of electrons in dome-shaped GeSi/Si islands. <i>Applied Physics Letters</i> , 2015, 106, 032104.	1.5	15
43	Raman scattering study of Ge dot superlattices. <i>Applied Surface Science</i> , 2001, 175-176, 629-635.	3.1	14
44	Hopping Conductivity and Coulomb Correlations in 2D Arrays of Ge <sup>s</sup> -Si Quantum Dots. <i>Journal of Experimental and Theoretical Physics</i> , 2005, 100, 722.	0.2	14
45	Excitons in Ge/Si double quantum dots. <i>JETP Letters</i> , 2009, 90, 569-573.	0.4	14
46	Near-infrared photoresponse in Ge/Si quantum dots enhanced by localized surface plasmons supported by aluminum nanodisks. <i>Journal of Applied Physics</i> , 2020, 128, 143101.	1.1	14
47	Quantum dot based mid-infrared photodetector enhanced by a hybrid metal-dielectric optical antenna. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 335105.	1.3	14
48	Ge/Si quantum-dot metal-oxide-semiconductor field-effect transistor. <i>Applied Physics Letters</i> , 2002, 80, 4783-4785.	1.5	13
49	Hydrogen passivation of self-assembled Ge/Si quantum dots. <i>Semiconductor Science and Technology</i> , 2014, 29, 085011.	1.0	13
50	Ge/Si waveguide photodiodes with built-in layers of Ge quantum dots for fiber-optic communication lines. <i>Semiconductors</i> , 2004, 38, 1225-1229.	0.2	12
51	Asymmetry of single-particle hole states in a strained Ge/Si double quantum dot. <i>Physical Review B</i> , 2008, 78, .	1.1	12
52	Formation of zero-dimensional hole states during molecular-beam epitaxy of Ge on Si (100). <i>JETP Letters</i> , 1998, 68, 135-141.	0.4	11
53	Hopping Transport through an Ensemble of Ge Self-Assembled Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , 2000, 218, 99-105.	0.7	11
54	Growth and characterization of CaF <sub>2</sub> /Ge/CaF <sub>2</sub> /Si(111) quantum dots for resonant tunneling diodes operating at room temperature. <i>Applied Physics Letters</i> , 2002, 81, 499-501.	1.5	11

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55	Determination of the composition and strains in $\text{Ge}_x\text{Si}_{1-x}$ -based nanostructures from Raman spectroscopy data with consideration of the contribution of the heterointerface. <i>Semiconductors</i> , 2007, 41, 930-934.	0.2	11
56	Comparison of two-dimensional arrays of gold disks and holes for plasmonic enhancement of Ge/Si quantum dot mid-infrared photodetectors. <i>Optical Materials Express</i> , 2018, 8, 3479.	1.6	11
57	Ge $\delta$ -Si Photodiodes and Phototransistors with Embedded Arrays of Germanium Quantum Dots for Fiber-Optic Communication Lines. <i>Physics of the Solid State</i> , 2005, 47, 34.	0.2	10
58	Photoconduction in tunnel-coupled Ge/Si quantum dot arrays. <i>Journal of Experimental and Theoretical Physics</i> , 2006, 103, 269-277.	0.2	10
59	Ge/Si heterostructures with Ge quantum dots for mid-infrared photodetectors. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2013, 49, 467-475.	0.2	10
60	Oscillations of hopping conductance in an array of charge-tunable self-assembled quantum dots. <i>Journal of Physics Condensed Matter</i> , 1999, 11, 9715-9722.	0.7	9
61	Modification of quantum dots in Ge/Si nanostructures by pulsed laser irradiation. <i>Semiconductors</i> , 2006, 40, 202-209.	0.2	9
62	Photovoltaic Ge/Si quantum dot detectors operating in the mid-wave atmospheric window (3 to 5 $\mu\text{m}$ ). <i>Nanoscale Research Letters</i> , 2012, 7, 494.	3.1	9
63	Strain-induced localization of electrons in layers of the second-type Ge/Si quantum dots. <i>JETP Letters</i> , 2015, 101, 750-753.	0.4	9
64	Near-Infrared Photoresponse in Ge/Si Quantum Dots Enhanced by Photon-Trapping Hole Arrays. <i>Nanomaterials</i> , 2021, 11, 2302.	1.9	9
65	Spontaneous fluctuations of variable-range hopping current in amorphous silicon microstructures. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1993, 179, 131-134.	0.9	8
66	Effect of Spin-Glass Ordering on Conduction in $a\text{-Si}_{1-x}\text{Mn}_x$ near the Metal-Insulator Transition. <i>Physica Status Solidi (B): Basic Research</i> , 1998, 205, 299-303.	0.7	8
67	Negative interband photoconductivity in Ge/Si heterostructures with quantum dots of the second type. <i>JETP Letters</i> , 2000, 72, 186-189.	0.4	8
68	Spatially indirect excitons in self-assembled Ge/Si quantum dots. <i>Nanotechnology</i> , 2001, 12, 441-446.	1.3	8
69	The Meyer-Neldel rule in the processes of thermal emission and hole capture in Ge/Si quantum dots. <i>JETP Letters</i> , 2004, 80, 321-325.	0.4	8
70	Midinfrared photoresponse of Ge quantum dots on a strained $\text{Si}_{0.65}\text{Ge}_{0.35}$ layer. <i>Semiconductor Science and Technology</i> , 2011, 26, 085018.	1.0	8
71	Antibonding ground state of holes in double vertically coupled Ge/Si quantum dots. <i>JETP Letters</i> , 2012, 94, 744-747.	0.4	8
72	Hopping conduction and resonant tunnelling in amorphous silicon microstructures. <i>Journal of Physics Condensed Matter</i> , 1994, 6, 2583-2594.	0.7	7

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73	Binding of electron states in multilayer strained Ge/Si heterostructures with type-II quantum dots. JETP Letters, 2006, 83, 156-161.	0.4	7
74	Suppression of hole relaxation in small Ge/Si quantum dots. JETP Letters, 2015, 102, 594-598.	0.4	7
75	Silicon-Based Nanoheterostructures With Quantum Dots. , 2017, , 59-99.		7
76	Metal-insulator transition in amorphous Si <sub>1-x</sub> C <sub>x</sub> Mnc obtained by ion implantation. JETP Letters, 1997, 65, 354-358.	0.4	6
77	Localization of electrons in multiple layers of self-assembled GeSi <sub>1-x</sub> Si islands. Applied Physics Letters, 2006, 89, 163126.	1.5	6
78	Bonding state of a hole in Ge/Si double quantum dots. JETP Letters, 2007, 86, 478-481.	0.4	6
79	MBE growth of ultra small coherent Ge quantum dots in silicon for applications in nanoelectronics. Journal of Physics and Chemistry of Solids, 2008, 69, 669-672.	1.9	6
80	Electromodulated reflectance study of self-assembled Ge/Si quantum dots. Nanoscale Research Letters, 2011, 6, 208.	3.1	6
81	Longitudinal conductivity of Ge/Si heterostructures with quantum dots. JETP Letters, 1996, 63, 444-447.	0.4	5
82	Current-voltage characteristics of porous amorphous Si <sub>1-x</sub> Mnx in the one-dimensional hopping regime. Philosophical Magazine Letters, 1996, 73, 17-26.	0.5	5
83	Contribution of the electron-electron interaction to the optical properties of dense arrays of Ge/Si quantum dots. Journal of Experimental and Theoretical Physics, 2001, 92, 500-513.	0.2	5
84	Quantum dot Ge/Si heterostructures. Physics-Usppekhi, 2001, 44, 1304-1307.	0.8	5
85	GERMANIUM SELF-ASSEMBLED QUANTUM DOTS IN SILICON FOR MID-INFRARED PHOTODETECTORS. International Journal of High Speed Electronics and Systems, 2002, 12, 873-889.	0.3	5
86	Many-particle effects in excitonic transitions in type-II Ge/Si quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1026-1029.	1.3	5
87	Si <sub>1-x</sub> Ge <sub>x</sub> /GaAs Nanoheterostructures for Photovoltaic Cells. Physics of the Solid State, 2005, 47, 63.	0.2	5
88	Hole states in artificial molecules formed by vertically coupled Ge/Si quantum dots. JETP Letters, 2007, 85, 429-433.	0.4	5
89	Infrared absorption and admittance spectroscopy of Ge quantum dots on a strained SiGe layer. Semiconductor Science and Technology, 2011, 26, 125002.	1.0	5
90	Self-assembled strained GeSiSn nanoscale structures grown by MBE on Si(100). Journal of Crystal Growth, 2017, 457, 215-219.	0.7	5

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91	Barrier height and tunneling current in Schottky diodes with embedded layers of quantum dots. JETP Letters, 2002, 75, 102-106.	0.4	4
92	Pulsed-laser modification of germanium nanoclusters in silicon. Semiconductors, 2003, 37, 1315-1320.	0.2	4
93	Ge/Si quantum dots in external electric and magnetic fields. Physics of the Solid State, 2004, 46, 56-59.	0.2	4
94	AC-hopping conductance of self-organized Ge/Si quantum dot arrays. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 450-454.	1.3	4
95	Hopping magnetoresistance in two-dimensional arrays of Ge/Si quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 296-299.	0.8	4
96	Molecular ground hole state of vertically coupled GeSi/Si self-assembled quantum dots. Nanotechnology, 2008, 19, 055202.	1.3	4
97	Influence of delta-doping on the hole capture probability in Ge/Si quantum dot mid-infrared photodetectors. Nanoscale Research Letters, 2014, 9, 504.	3.1	4
98	On the process of hole trapping in Ge/Si heterostructures with Ge quantum dots. Semiconductors, 2014, 48, 1036-1040.	0.2	4
99	Plasmonic Field Enhancement by Metallic Subwave Lattices on Silicon in the Near-Infrared Range. JETP Letters, 2019, 110, 411-416.	0.4	4
100	Increase in the Photocurrent in Layers of Ge/Si Quantum Dots by Modes of a Two-Dimensional Photonic Crystal. JETP Letters, 2021, 113, 498-503.	0.4	4
101	The Kondo effect in amorphous. Journal of Physics Condensed Matter, 1997, 9, 499-506.	0.7	3
102	Suppression of the fractal conductivity channel and superlocalization effects in porous a-Si:H. Journal of Experimental and Theoretical Physics, 1997, 85, 501-506.	0.2	3
103	One-dimensional localization in porous a-Si $\hat{c}$ Mnc. JETP Letters, 1998, 67, 284-288.	0.4	3
104	Interlevel optical transitions and many-body effects in a dense array of Ge/Si quantum dots. Thin Solid Films, 2000, 380, 82-85.	0.8	3
105	Ge dots on Si (111) and (100) surfaces with SiO <sub>2</sub> coverage: Raman study. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 23, 320-323.	1.3	3
106	Photoinduced and equilibrium optical absorption in Ge/Si quantum dots. Semiconductors, 2012, 46, 1529-1533.	0.2	3
107	Intraband optical transitions of holes in strained SiGe quantum wells. JETP Letters, 2013, 97, 159-162.	0.4	3
108	Bidirectional photocurrent of holes in layers of Ge/Si quantum dots. JETP Letters, 2014, 100, 91-94.	0.4	3

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109	The temperature-induced transition from 3d to 1d hopping conduction in porous amorphous. Journal of Physics Condensed Matter, 1997, 9, 889-899.	0.7	2
110	Local structure of self-organized uniform Ge quantum dots on Si(001). Solid State Ionics, 2001, 141-142, 135-139.	1.3	2
111	Many-electron Coulomb correlations in hopping transport along layers of quantum dots. JETP Letters, 2003, 78, 241-245.	0.4	2
112	Hopping photoconduction and its long-time kinetics in a heterosystem with Ge quantum dots in Si. JETP Letters, 2003, 78, 587-591.	0.4	2
113	GERMANIUM SELF-ASSEMBLED QUANTUM DOTS IN SILICON FOR MID-INFRARED PHOTODETECTORS. Selected Topics in Electronics and Systems, 2003, , 281-297.	0.2	2
114	Self-assembling of Ge quantum dots in the CaF2/Ge/CaF2/Si heteroepitaxial system and the development of tunnel-resonance diode on its basis. Physics of the Solid State, 2004, 46, 89-91.	0.2	2
115	Two-dimensional phononless VRH conduction in arrays of Ge/Si quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 51-54.	0.8	2
116	Molecular epitaxy and the electronic properties of Ge/Si heterosystems with quantum dots. Low Temperature Physics, 2004, 30, 877-884.	0.2	2
117	Quantum Dots Microstructure and Energy Spectrum Peculiarities. Physica Scripta, 2005, , 439.	1.2	2
118	MBE growth of vertically ordered Ge quantum dots on Si. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 262-264.	0.8	2
119	Double-occupancy probability and entanglement of two holes in double Ge/Si quantum dots. JETP Letters, 2010, 92, 36-39.	0.4	2
120	Valence-band offsets in strained SiGeSn/Si layers with different tin contents. Semiconductors, 2017, 51, 329-334.	0.2	2
121	Development of a high-voltage waveguide photodetector comprised of Schottky diodes and based on the Ge/Si structure with Ge quantum dots for portable thermophotovoltaic converters. Optoelectronics, Instrumentation and Data Processing, 2017, 53, 190-196.	0.2	2
122	Enhanced Optical Properties of Silicon Based Quantum Dot Heterostructures. Defect and Diffusion Forum, 2018, 386, 68-74.	0.4	2
123	Wide coulomb gap in localized states of 3d-metals in amorphous silicon. Journal of Non-Crystalline Solids, 1987, 90, 111-114.	1.5	1
124	Inelastic resonant tunneling in amorphous silicon microstructures. Physics Letters, Section A: General, Atomic and Solid State Physics, 1994, 194, 133-136.	0.9	1
125	Anisotropic negative magnetoresistance in one-dimensional channels of porous silicon. JETP Letters, 1999, 69, 202-206.	0.4	1
126	Non-equilibrium transport in arrays of type-II Ge/Si quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 21-24.	0.8	1



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127	Hopping photoconductivity and its long-time relaxation in two-dimensional array of Ge/Si quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 3118-3121.	0.8	1
128	Raman scattering diagnostics of as grown and pulsed laser modified Ge-Si nanostructures with quantum dots. , 2007, , .		1
129	SiGe Nanodots in Electro-Optical SOI Devices. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , 2007, , 113-128.	0.2	1
130	Hole states in vertically coupled double Ge/Si quantum dots. <i>Microelectronics Journal</i> , 2009, 40, 785-787.	1.1	1
131	Light absorption related to hole transitions in quantum dots and impurity centers in quantum wells under external excitation. <i>Journal of Physics: Conference Series</i> , 2009, 193, 012059.	0.3	1
132	Strain-dependent intersubband absorption in the valence band of SiGe quantum wells. <i>Semiconductor Science and Technology</i> , 2014, 29, 045008.	1.0	1
133	Simulation-Based Multi-Criterion Approach to Production Processes Control. <i>IFAC-PapersOnLine</i> , 2017, 50, 15580-15585.	0.5	1
134	Energy Spectrum of Charge Carriers in Elastically Strained Assemblies of Ge/Si Quantum Dots. <i>Journal of Surface Investigation</i> , 2018, 12, 306-316.	0.1	1
135	Effect Of Light Illumination On The Conductivity Of Tunnel-coupled Ge/Si Quantum Dots. <i>AIP Conference Proceedings</i> , 2007, , .	0.3	1
136	Photostimulated mesoscopic current fluctuations in a-Si based microstructures. <i>JETP Letters</i> , 1996, 64, 724-728.	0.4	0
137	Mesoscopic Phenomena in a-Si Based Microstructures. <i>Physica Status Solidi (B): Basic Research</i> , 1998, 205, 193-198.	0.7	0
138	Mechanism of Two-Level Hopping Current Fluctuations in Mesoscopic a-Si Based Structures. <i>Physica Status Solidi (B): Basic Research</i> , 2000, 218, 155-158.	0.7	0
139	<title>Hole transport in Ge/Si quantum dot field-effect transistors</title>. , 2002, , .		0
140	STARK SPECTROSCOPY OF Ge/Si(001) SELF-ASSEMBLED QUANTUM DOTS. <i>International Journal of Nanoscience</i> , 2003, 02, 505-510.	0.4	0
141	Developing XAFS Method Designed for Characterization of Materials Containing Nanostructures (Ge/Si Systems). <i>AIP Conference Proceedings</i> , 2003, , .	0.3	0
142	Mechanisms of low-temperature high-frequency conductivity in systems with a dense array of Ge <sub>0.7</sub> Si <sub>0.3</sub> quantum dots in silicon. <i>Journal of Experimental and Theoretical Physics</i> , 2005, 101, 1122-1129.	0.2	0
143	Acoustoelectric Effects in Ge/Si Nanosystems with Ge Quantum Dots. <i>AIP Conference Proceedings</i> , 2005, , .	0.3	0
144	AC Conductance in Dense Array of the Ge <sub>0.7</sub> Si <sub>0.3</sub> Quantum Dots in Si. <i>AIP Conference Proceedings</i> , 2006, , .	0.3	0

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145	SPACE-CHARGE SPECTROSCOPY OF ELECTRONIC STATES IN Ge/Si QUANTUM DOTS WITH TYPE-II BAND ALIGNMENT. International Journal of Nanoscience, 2007, 06, 353-356.	0.4	0
146	PULSED LASER ANNEALING OF Ge/Si HETEROSTRUCTURES WITH QUANTUM DOTS. , 2007, , .		0
147	Localization of electrons in type-II Ge/Si quantum dots stacked in a multilayer structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 442-444.	0.8	0
148	Influence of pulsed laser annealing on the properties of Ge quantum dots in Si matrix. Proceedings of SPIE, 2008, , .	0.8	0
149	Physics and technology of quantum dot semiconductor nanostructures for IR application. Bulletin of the Russian Academy of Sciences: Physics, 2009, 73, 66-69.	0.1	0
150	Investigation of time characteristics of photodetectors based on Ge/Si nanoheterostructures. Russian Physics Journal, 2010, 53, 504-507.	0.2	0
151	Electronic structure of double Ge quantum dots in Si. JETP Letters, 2012, 96, 75-83.	0.4	0
152	Enhancement of the hole photocurrent in layers of Ge/Si quantum dots with abrupt heterointerfaces. JETP Letters, 2016, 104, 479-482.	0.4	0
153	Selective enhancement of the hole photocurrent by surface plasmonâ€“polaritons in layers of Ge/Si quantum dots. JETP Letters, 2017, 105, 426-429.	0.4	0
154	Localization of Surface Plasmon Waves in Hybrid Photodetectors with Subwavelength Metallic Arrays. JETP Letters, 2018, 108, 374-378.	0.4	0
155	Plasmon Enhancement of the Electric Field in Mid-Infrared Ge/Si Quantum-Dot Photodetectors with Different Thicknesses of the Active Region. Semiconductors, 2019, 53, 195-199.	0.2	0
156	Optical Properties Of Arrays Of Ge/Si Quantum Dots In Electric Field. , 2003, , 307-314.		0
157	Quantum Dot Array Energy Spectrum Tuning With Laser Pulse Action. AIP Conference Proceedings, 2007, , .	0.3	0
158	Effect of Adhesive Layers on Photocurrent Enhancement in Near-Infrared Quantum-Dot Photodetectors Coupled with Metal-Nanodisk Arrays. Semiconductors, 2021, 55, 654.	0.2	0